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IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Inventors:	Huiling Zhu et al.	Date:	3 May 2005
Serial No.:	10/605,726	Art Unit:	2813
Filing Date:	22 October 2003	Examiner:	Stephen W. Smoot
Confirmation No.:	2725	Docket No.	FIS9-2003-0303-US1
Title:	Method of Manufacture of Thin Silicon on Insulator (SOI) with Recessed Channel and Devices Manufactured Thereby	Attorney:	Graham S. Jones, II 42 Barnard Avenue Poughkeepsie, NY 12603-5023

AMENDMENT

The Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

Your Honor:

In response to the Office Action of 8 February 2005, please amend the above-identified application as follows:

Amendments to the Title	begin on page	2	of this paper.
Amendments to the Abstract	begin on page	3	of this paper
Amendments to the Specification	begin on page	4	of this paper
Amendments to the Claims	begin on page	12	of this paper.
Remarks/Arguments	begin on page	18	of this paper.

Serial No.:	10/605,726	Art Unit:	2813
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IN THE TITLE

Please amend the title to read as follows:

**Method of Manufacture of Thin Silicon on Insulator (SOI) with Recessed Channel
~~and Devices Manufactured Thereby~~**